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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/775,231	02/01/2001	Han-Sin Lee	SAM-167	9048
7:	590 03/23/2004		EXAMINER	
MILLS & ONELLO, LLP			POMPEY, RON EVERETT	
ELEVEN BEA	CON STREET		ART UNIT PAPER NUMBER	
BOSTON, MA	02108		2812	
			DATE MAILED: 03/23/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	-			
	09/775,231	LEE ET AL.	į			
Office Action Summary	Examiner	Art Unit				
	Ron E Pompey	2812				
The MAILING DATE of this communication ap Period for Reply	ppears on the cover sheet with the	correspondence address				
A SHORTENED STATUTORY PERIOD FOR REPORTED MAILING DATE OF THIS COMMUNICATION  - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply be tiply within the statutory minimum of thirty (30) dated will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDON.	mely filed ys will be considered timely. n the mailing date of this communicat ED (35 U.S.C. § 133).	ion.			
Status						
1) Responsive to communication(s) filed on 201	February 2004.					
	is action is non-final.					
3) Since this application is in condition for allow	3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.				
Disposition of Claims	·					
4)  Claim(s) 1,2 and 4-13 is/are pending in the a 4a) Of the above claim(s) is/are withdres 5)  Claim(s) is/are allowed. 6)  Claim(s) 1-2 and 4-13 is/are rejected. 7)  Claim(s) is/are objected to. 8)  Claim(s) are subject to restriction and/ Application Papers  9)  The specification is objected to by the Examination of the drawing(s) filed on is/are: a) and applicant may not request that any objection to the	awn from consideration.  for election requirement.  her. hercepted or b) □ objected to by the herce drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the E	-xaminer. Note the attached Oπic	e Action of form P1O-152.				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of:  1. Certified copies of the priority documer 2. Certified copies of the priority documer 3. Copies of the certified copies of the pri application from the International Bure. * See the attached detailed Office action for a list	nts have been received. nts have been received in Applica ority documents have been receiv au (PCT Rule 17.2(a)).	tion No ved in this National Stage				
Attachment(s)	4) 🔲 Interview Summar	v (PTO_413)				
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date</li> </ol>	Paper No(s)/Mail [					

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 1, 2 and 4-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laparra et al. (US 6,319,796) and in further view of Park et al. (US 6,326,282) and Shin et al. (US 6,184,077).

Laparra discloses the steps of:

For claims 1, 2 and 4-6:

etching the exposed semiconductor substrate, using the etching mask pattern as an etching mask, to form a trench;

providing a material layer (40b, fig. 4) on the insulating layer (40a, fig. 4) filling the trench;

planarly etching the material layer and the insulating layer down to a top surface of the etching mask pattern to form a device isolation layer pattern in the trench; and removing the exposed etching mask pattern (col. 4, Ins. 5-10 and col. 5, Ins. 51-56).

Laparra discloses all the steps of claims 1-12 except those described below.
 However Park discloses the steps of:

For claims 8-12:

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prior to forming the insulating layer:

forming an oxide layer (112, fig, 2D) on the inner wall and bottom of the trench; forming an oxidation barrier layer (114, fig. 2D) on the oxide layer; and further comprising forming a capping layer (115, fig. 2D) between the oxidation barrier layer and the insulating layer (col. 4, Ins. 29-52).

Therefore it would have been obvious to those of ordinary skill in the art to combine Park with Laparra, because the layers disclosed by Park are protection layers for the trench.

4. Laparra and Park disclose all the steps of claims 1, 2 and 4-12 except for the material layer being formed being formed at a temperature of 700°C - 800°C and forming a etch-stop layer comprising polysilicon and a HTO layer which are sequentially stacked. However, Shin, column 5, lines 12-18, discloses that an LPCVD method comprises forming monosilane and dichlorosilane HTO and TEOS films at high temperatures in the range claimed by applicant. Therefore, Shin provides a specific temperature for different LPCVD layer, HTO and TEOS films, whereas Laparra just discloses the general conditions that the layer 40b is formed by a LPCVD method, which includes, but not limited to, TEOS. Park even says, column 3, lines 14-15, state that, "A high temperature oxide layer such as HTO and LP-TEOS oxide layers...", HTO and LP-TEOS layers form high temperature oxides. Therefore, from these two references HTO and LP-TEOS are considered as art equivalent layers. Also, that it would have been obvious to one having ordinary skill in the art at the time the invention was made to form an etch-stop layer, comprising polysilicon and a HTO layer which are

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sequentially stacked, since it has been held to be within the general skill of a worker in the art to select a known material on the basis of its suitability for the intended use as a matter of obvious design choice. In re Leshin, 125 USPQ 416.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E Pompey whose telephone number is (571) 272-1680. The examiner can normally be reached on flex schedule.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Ron Pompey AU:2812

March 21, 2004

John F. Niebling
Supervisory Patent Examiner
Technology Center 2800

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